Flash Photolysis Study for Halogen Abstraction of Ph₃Sn and Ph₃Si from Alkyl Halides

Osamu Ito* Kiyohiko Hoteiya, Akira Watanabe, and Minoru Matsuda Chemical Research Institute of Non-Aqueous Solutions, Tohoku University, Katahira, Aoba-ku, Sendai 980 (Received September 6, 1990)

The reaction rate constants for halogen abstraction of $Ph_3Sn \cdot$ and $Ph_3Si \cdot$ have been determined by xenonflash photolysis method. The absolute rate constants for the reactivity of $Ph_3Sn \cdot$ with several alkyl halides have been compared with the relative ones; the agreement between the both methods was fairly good. For $Ph_3Sn \cdot$, the rate constant (in unit of mol^{-1} dm³ s⁻¹) of n-BuCl (5.2×10^2) was smaller than that of n-BuBr (3.1×10^6) by a factor of ca. $1/10^4$. With changing the alkyl halides, the rate constants for $Ph_3Si \cdot$ and $Ph_3Sn \cdot$ varied similarly, although the rate constants for $Ph_3Si \cdot$ were larger than those for $Ph_3Sn \cdot$ by factors of 50—100. The reactivity of alkyl halides increased with a decrease in the bond-dissociation energy of the R-X (X=Cl, Br).

The high reactivities of organostannyl and organosilyl radicals in halogen abstraction reactions have been well-known and utilized widely in synthetic chemistry.1) The relative reactivities were evaluated by various methods such as product analysis²⁾ and ESR spectroscopy.³⁾ Some of them were converted into absolute rate constants by Carlsson and Ingold using the rotating sector/competitive method.⁴⁾ In order to obtain the absolute rate constants, the laser-flash photolysis has been applied to radical reactions including the organometallic radicals.5-10) Although the usefulness of this method has been widely proved, it is hard to evaluate the rate constants smaller than ca. 10⁵ mol⁻¹ dm³ s⁻¹. For such relatively slow reactions, the xenon-flash photolysis would be expected to be useful.11,12)

In this study, we report the absolute rate constants evaluated by following the direct decay of transient absorption bands due to Ph₃Sn· and Ph₃Si· in the presence of various alkyl halides. The absolute rate constants thus evaluated are compared with the relative rate constants obtained by a competitive method. Furthermore, we attempted to clarify the factors determining the reactivities.

Experimental

 $Ph_3SnSnPh_3$ and $Ph_3SiSiPh_3$ used as the radical sources were prepared by refluxing Ph_3MCl (M=Sn, Si) with sodium metal in toluene under N_2 .¹³⁾ Alkyl halides and solvents were purified by distillation before use.

Xenon-flash photolysis apparatus was of the standard design equipped with two xenon-flash lamps (Xenon Corp., N-851C); the half-duration of the lamp was ca. 8 μ s. The solution containing the radical source was photodecomposed with the light longer than 270 nm which was selected by the cut-off light filter; thus, alkyl halides having absorption band shorter than 270 nm were chosen as substrates in this study. The solution was degassed up to ca. 10^{-2} Pa. All measurements were performed at 23 °C.

For competitive experiments to evaluate the relative reaction rate constants, the following chain reactions were used (Scheme 1).

$$(CH_3)_2(CN)CN=NC(CN)(CH_3)_2 \xrightarrow{h\nu}$$

$$2 (CH_3)_2(CN)C \cdot + N_2$$
 (1)

$$(CH_3)_2(CN)C \cdot + Ph_3SnH \longrightarrow$$

$$Ph_3Sn \cdot + (CH_3)_2(CN)CH \quad (2)$$

$$Ph_{3}Sn \cdot + RX \xrightarrow{k_{x}^{r}} Ph_{3}SnX + R.$$
 (3)

$$R \cdot + Ph_3SnH \longrightarrow RH + Ph_3Sn$$
. (4)

Scheme 1.

By using azobisisobutyronitrile as a photo-initiator, which was decomposed with the light longer wavelength than 350 nm, one could obtain the relative rates for the alkyl halides with absorption band at longer wavelength than 270 nm. For such alkyl halides, it was difficult to obtain the absolute rate constants by the xenon-flash photolysis method. RH and RX were analyzed by gas chromatography; the relative rate constants were computed by the Ingold and Shaw method.¹⁴⁾

Results and Discussion

Figure 1 shows the transient absorption spectra produced by the flash photolysis of Ph₃SnSnPh₃ and Ph₃SiSiPh₃ in degassed cyclohexane solution. The main peak appeared at 320—330 nm with the broad band near 450 nm. The main peaks at 320—330 nm are similar to the reported absorption bands for Ph₃Sn· and Ph₃Si· by Chatgilialoglu et al.⁸⁾

$$Ph_{3}MMPh_{3} \xrightarrow[k_{b}]{h\nu} 2 Ph_{3}M.$$

$$(M = Si, Sn)$$
(5)

By the photolysis of some disilanes and digermanes, the biradical formation via the ipso addition was reported.^{10,15)} It is presumed that these species also show the absorption band at ca. 330 nm, although the decay rate was slower than that of the metal centered radicals.¹⁰⁾ However, in the case of photolysis of

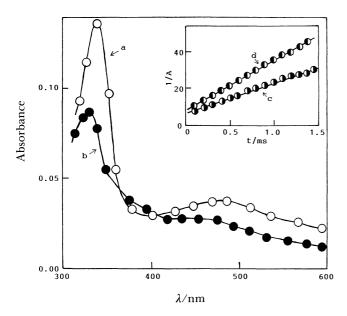


Fig. 1. Transient absorption spectra immediately after flash photolysis of 10⁻⁴ mol dm⁻³ of (a) Ph₃SiSiPh₃ and (b) Ph₃SnSnPh₃ in degassed cyclohexane in a cylindrical flash cell (10 cm optical path). Insert: Second-order plot at 330 nm of Ph₃Sn·; (c) in cyclohexane and (d) in hexane.

Ph₃SnSnPh₃ and Ph₃SiSiPh₃, the formation of the biradicals may not be the main path because of the steric hindrance of many phenyl groups. The broad weak absorption band near 450 nm produced by the photolysis of the disilane was attributed to the free silanediyl (R₂Si:),¹⁶⁾ or to the rearrangement product.¹⁷⁾

When *n*-donor solvent was used, the absorption of R₂Si: shifts to 320—330 nm by the complex formation.¹⁸⁾ Thus, we used cyclohexane as a solvent throughout this study. We followed predominately the decay of the main band at 320—330 nm to determine the reaction rates of Ph₃Sn· and Ph₃Si· with alkyl halides.

The insert of Fig. 1 shows the second-order plots (1/absorbance vs. time) for Ph₃Sn. The linear lines indicate that Ph₃Sn predominately returns to Ph₃Sn-SnPh₃. The slope of the second-order plot, which refers to the ratio of $2k_b$ to the extinction coefficient (ε), varies with solvent viscosity, suggesting that k_b is near a diffusion controlled limit. The $2k_b/\varepsilon$ value in hexane is 3.5×10⁵ cm⁻¹ s⁻¹, which is close to the reported one by the laser flash photolysis.8) assuming $k_b = ca. 2 \times 10^9 \text{ mol}^{-1} \text{ dm}^3 \text{ s}^{-1}$ which is about a half of $(C_2H_5)_3Si$, ε can be calculated to be ca. 104 cm⁻¹ mol⁻¹ dm³; thus, the initial concentration of Ph₃Sn· produced by one flash exposure can be calculated from Fig. 1 to be ca. 10⁻⁶ mol dm⁻³. In the case of Ph₃Si., the decay kinetics deviated from the second-order kinetics, suggesting that Ph₃Si· reacts with the phenyl group of the radical source.⁸⁾ On

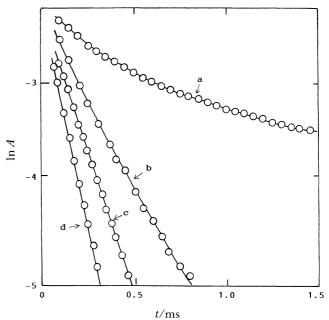


Fig. 2. First-order plots for decay of Ph_8Sn (at $330\,\mathrm{nm}$) in the presence of t-BuCl in degassed cyclohexane; (a) 0, (b) 0.21, (c) 0.47, and (d) 0.70 mol dm⁻³.

addition of small amount of oxygen, $Ph_3Sn \cdot$ and $Ph_3Si \cdot$ decayed rapidly; the rate constant for this reaction may be larger than $10^9 \, \text{mol}^{-1} \, \text{dm}^3 \, \text{s}^{-1}$.

By the addition of appropriate concentration of alkyl halides to degassed solution, decay kinetics of Ph_3Sn changed into first-order kinetics as shown in Fig. 2 for the reaction with *t*-butyl chloride. The decay rates were accelerated by the addition of the alkyl hafides; thus, the following halogen abstraction reaction occurs.

$$Ph_3M \cdot + RX \xrightarrow{k_X} Ph_3MX + R \cdot$$
 (6)

When the concentration of RX was properly high, the first-order part became predominant as shown in Fig. 2, in which the slope refers to as $k_{\rm first-order}$. When the concentration of RX was low, the contribution of the first-order term to the whole decay was small; for such case, the first-order term was separated from the mixed-order kinetics by a computer simulation method.^{19,20)} Figure 3 shows the pseudo-first-order plots for some reaction systems; the slope gave the $k_{\rm X}$ value. The $k_{\rm X}$ values for various alkyl halides are summarized in Table 1 for Ph₃Sn· and Ph₃Si·.

The relative halogen abstraction reactivities (k_X^r) of alkyl halides by Ph_3Sn were determined by the competitive experiment described in the experimental section. They are also summarized in Table 1, in which the k_X^r value of CH_2Cl_2 was set to be 1.0. In Fig. 4, these k_X^r values are plotted against the k_X values; a linear relation is seen, showing the reliability of the

	Abstraction of Ph ₃ Sn· and Ph ₃ Si· from RX in Cyclohexane at 23 °C				
	Ph₃Sn•	Ph₃Si•	71		
D 37	, a)	7 a)	11		

	Ph₃Sn∙		Ph₃Si•	TEs)
RX	$\frac{k_{x}^{a)}}{\text{mol}^{-1} \text{dm}^{3} \text{s}^{-1}}$	$k_{\mathrm{x}}^{\mathrm{r}^{\mathrm{b}}}$	$\frac{k_{x}^{a)}}{\text{mol}^{-1}\mathrm{dm}^{3}\mathrm{s}^{-1}}$	—————————————————————————————————————
n-BuCl	5.2×10 ²	0.038	6.3×10 ⁴	10.67
c-C ₆ H ₁₁ Cl		0.054		
$(CH_2Cl)_2$	4.5×10^{3}	0.15	5.7×10^{5}	11.12
t-BuCl	1.4×10^{4}	0.43	8.0×10^{5}	10.61
CH_2Cl_2	3.2×10^{4}	1.0	3.4×10^{6}	11.35
PhCH ₂ Cl		7.7		9.17
$CHCl_3$	2.0×10^{6}	55	1.1×10^{8}	11.42
$n ext{-BuBr}$	3.1×10^{6}	150		10.125
c-C ₆ H ₁₁ Br		250		

a) Each k_x value contains estimated error of ca. 10%. b) Estimation error of k_x^x is ca. 5%. c) Ionization energy from "Handbook of Chemistry and Physics," CRC Press, Bacon Raton, FL (1984), p. E-40.

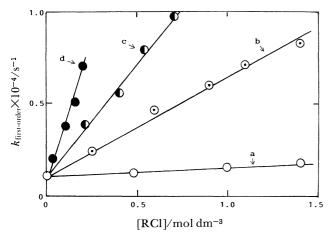


Fig. 3. Plots of pseudo-first-order rate constants $(k_{\text{first-order}})$ of Ph₃Sn· vs. concentration of alkyl halides; (a) n-BuCl, (b) (CH₂Cl)₂, (c) t-BuCl, and (d) CH₂Cl₂.

reaction rate constants obtained by the both methods. The k_X value for the reaction system of Ph₃Sn \cdot -t-BuCl obtained in this study (1.4×104 mol-1 dm3 s-1) was similar to the reported one $(2.0\times10^4 \,\mathrm{mol^{-1}\,dm^3\,s^{-1}})$ which was determined with the rotating sector/ESR method reported by Carlsson and Ingold.4)

For Ph₃Sn·, the following orders in the reactivities were confirmed; RCl<RBr, R_{primary}-Cl<R_{tertiary}-Cl< cyclic halide. In order to investigate the factor controlling the reactivities, the $k_{\rm X}$ values are plotted against the bond-dissociation energy (BDE) of R-X.21) In Fig. 5, linear correlations are found for the both radicals; the weaker the R-X bond is, the higher the reactivity is. A typical example is shown for the reactivity of RCl<RBr. Within the same halogen series, the low BDE value of R-X implies that the carbon radical $(R \cdot)$ is stable. Thus, the order of $R_{primary}$ -Cl< $R_{tertiary}$ -Cl is attributed to higher stability of tertiary carbon radical than the primary one. The α halogen effect is more effective than the β -effect

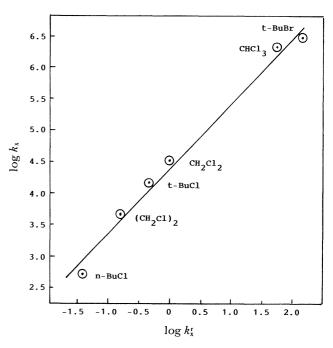


Fig. 4. Plot of $\log k_X$ (absolute rate constants) vs. $\log k_x^r$ (relative rate constant) for Ph₃Sn·.

 $[k_{\rm X}({\rm CH_2Cl_2})/k_{\rm X}(({\rm CH_2Cl_2}))={\rm ca.} 7].$ The α -effect is intensified with additional halogen atom [kx(CHCl3)/ $k_{\rm X}({\rm CH_2Cl_2})={\rm ca.~60}$]. Since the $k_{\rm r}$ values of these compounds are also on the line of Fig. 5, these effects can be interpreted by the stability of the carbon centered radicals; some of the resonance structures can be written as follows;

α-effect;
$$>\dot{c}-c1$$
 $>c-\dot{c}\dot{1}$
β-effect; $>\dot{c}-\dot{c}-\dot{c}$

As for the polar contribution to the transition states of these reactions, charge transfer from the radical

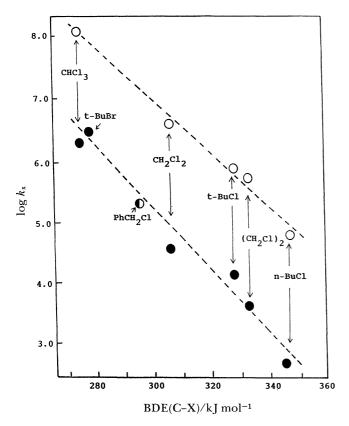


Fig. 5. Plots of $\log k_X$ vs. bond-dissociation energy of R-X [BDE(C-X)]. (\bullet) Ph₃Sn· and (O) Ph₃Si·; (\bullet) k_X for PhCH₂Cl was evaluated from Fig. 4.

center to RX has been presumed from the Hammett plot by Chatgilialoglu et al.²³⁾ In Table 1, however, no clear tendency that $k_{\rm X}$ values increase with the ionization energy can be found. This suggests that the polar effect is not the main factor in determining the reactivity, when a wide range of RX is compared.

From Table 1 and Fig. 5, it is confirmed that the reactivity of Ph₃Si· is higher than that of Ph₃Sn·; this tendency is in agreement with the order of reactivities in the halogen abstraction of *n*-Bu₃Sn· and Et₃Si·.⁸⁾ The order of the reactivity of R₃Sn· and R₃Si· can be well interpreted by the thermodynamic data; i.e., in the case of (CH₃)₃MCl, BDE of Sn-Cl (422 kJ mol⁻¹) is smaller than that of Si-Cl (485 kJ mol⁻¹),²⁴⁾ which indicates that Cl-abstraction of (CH₃)₃Sn· is more endothermic than that by (CH₃)₃Si·. Although the thermodynamic data for Ph₃MX are not available, this tendency is in good agreement with our observed tendency in the reactivities of Ph₃Sn· and Ph₃Si· for halogen abstraction.

The k_X value for $Ph_3Sn \cdot -n$ -BuBr is ca. 1/10 of n-Bu₃Sn · , in which the latter rate constant was determined by the laser-flash probe method.⁶⁾ The k_X value for $Ph_3Si \cdot -t$ -BuCl is also ca. 1/10 of $Et_3Si \cdot -t$ -BuCl.⁷⁾ The slightly lower reactivity of $Ph_3M \cdot$ compared with the corresponding $R_3M \cdot$ can be confirmed in this study. In the case of the $Ph_3C \cdot$ and

 R_3C_{\cdot} , the former is extremely less reactive than the latter, because of the delocalization of the unpaired electron into the phenyl groups even though the π -orbitals are not in the same plane. On the other hand, the delocalization of the unpaired electron would not be expected for Ph_3Sn_{\cdot} and Ph_3Si_{\cdot} , because of the small overlap between the orbitals of unpaired electron of the central atom [Si(3p) or Sn(5p)] and $phenyl\ 2p\text{-orbital}$. Thus, the difference in the reactivity between Ph_3M_{\cdot} and R_3M_{\cdot} is quite small.

References

- 1) a) H. G. Kuivila, L. W. Menapace, and C. R. Warner, *J. Am. Chem. Soc.*, **84**, 3584 (1963); b) H. G. Kuivila and L. W. Menapace, *J. Org. Chem.*, **28**, 2165 (1963).
- 2) L. W. Menapace and H. G. Kuivila, *J. Am. Chem. Soc.*, **86**, 3047 (1964).
- 3) J. Cooper, A. Hudson, and R. A. Jackson, J. Chem. Soc., Perkin Trans. 2, 1973, 1056.
- 4) D. J. Carlsson and K. U. Ingold, *J. Am. Chem. Soc.*, **90**, 7047 (1968).
- 5) H. Paul, R. D. Small, Jr., and J. C. Scaiano, J. Am. Chem. Soc., 100, 4520 (1978).
- 6) C. Chatgilialoglu, K. U. Ingold, and J. C. Scaiano, J. Am. Chem. Soc., **104**, 5123 (1982).
- 7) K. U. Ingold, J. Lusztyk, and J. C. Scaiano, J. Am. Chem. Soc., 106, 343 (1984).
- 8) C. Chatgilialoglu, K. U. Ingold, J. Lusztyk, A. S. Nazran, and J. C. Scaiano, *Organometallics*, **2**, 1332 (1983).
- 9) C. Chatgilialoglu, K. U. Ingold, J. C. Scaiano, and H. Woynar, J. Am. Chem. Soc., 103, 3231 (1981).
- 10) K. Mochida, M. Wakasa, Y. Nakadaira, Y. Sakaguchi, and H. Hayashi, *Organometallics*, 7, 1869 (1988).
- 11) O. Ito, J. Am. Chem. Soc., 105, 850 (1983).
- 12) O. Ito and M. Matsuda, J. Polym. Sci. Part. A, Polym. Chem. Ed., 28, 1947 (1990).
- 13) H. Gilman and S. D. Rosenberg, *J. Am. Chem. Soc.*, **74**, 531 (1952).
- 14) C. K. Ingold and F. R. Shaw, J. Chem. Soc., 1927, 2918.
- 15) H. Sakurai, J. Organomet. Chem., **200**, 261 (1980); **110**, 6270 (1988).
- 16) G. R. Gillette, G. H. Noren, and R. West, *Organometallics*, **6**, 2617 (1987).
- 17) H. Shizuka, K. Okazaki, M. Tanaka, M. Ishikawa, M. Sumitani, and K. Yoshihara, *Chem. Phys. Lett.*, **113**, 89 (1985).
- 18) T. Akasaka, S. Nagase, A. Yabe, and W. Ando, J. Am. Chem. Soc., 110, 6270 (1988).
- 19) E. F. Zwicker and L. I. Grossweiner, *J. Phys. Chem.*, **67**, 549 (1963).
- 20) G. L. Closs and B. E. Rabinow, J. Am. Chem. Soc., 98, 8190 (1976).
- 21) S. W. Benson, "Methods for the Estimation of Thermochemical Data and Rate Parameters," Wiley, New York (1971).
- 22) F. W. Evance and M. Szwarc, *Trans. Faraday Soc.*, **57**, 1905 (1961).
- 23) C. Chatgilialoglu, K. U. Ingold, and J. C. Scaiano, J. Org. Chem., **52**, 938 (1987).
- 24) R. A. Jackson, J. Organomet. Chem., 166, 17 (1979).